

FMMT449



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SuperSOT[™]-3

NPN Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous. Sourced from Process NB.

Absolute Maximum Ratings*

Symbol	Parameter	FMMT449	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous - Peak Pulse Current	1 2	А
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C
*These ratir	ngs are limiting values above which the serviceability of any semiconductor device	ce may be impaired.	, cot
NOTES:	atings are based on a maximum junction temperature of 150°C.	ce may be impaired.	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

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- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherw}

Symbol	Characteristic	Мах	Units
	The second second	FMMT449	
P _D	Total Device Dissipation* Derate above 25°C	500 4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

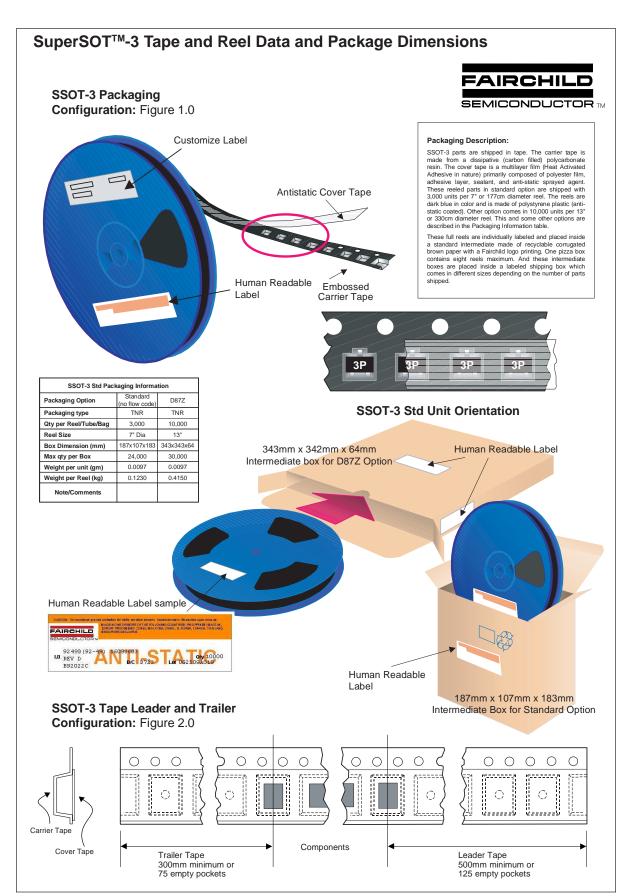
*Device mounted on FR-4 PCB 4.5" X 5"; mounting pad 0.02 in² of 2oz copper.

(continued)

Electrical Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	30		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1mA	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40 V V _{CB} = 40 V, Ta=100°C		100 10	nA uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	ACTERISTICS*			1	1
h _{FE}	DC Current Gain	I _C = 50 mA, V _{CE} = 2V	70		-
		$I_C = 500 \text{ mA}, V_{CE} = 2V$	100	300	
		$I_C = 1A$, $V_{CE} = 2V$	80		
		$I_C = 2A$, $V_{CE} = 2V$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		500	mV
0=(00.3)		I _C = 2 A, I _B = 200 mA		1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL SI	IGNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		15	pF
f _T	Transition Frequency	$I_C = 50 \text{mA}, V_{CE} = 10 \text{ V}, f = 100 \text{MHz}$	150		MHz

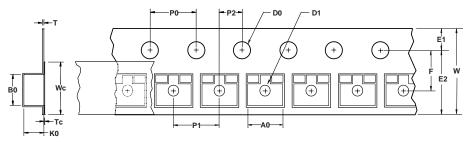
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

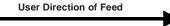


SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



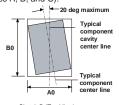


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



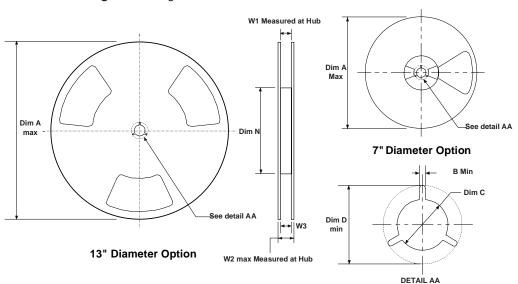
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

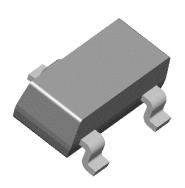
SSOT-3 Reel Configuration: Figure 4.0

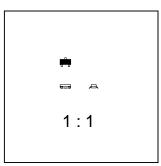


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

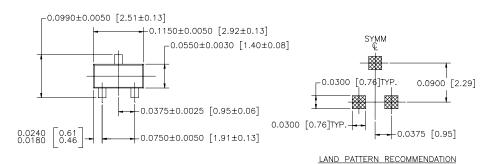
SuperSOT™-3 (FS PKG Code 32)

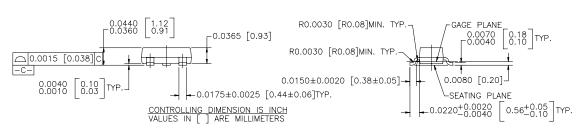




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097





NOTES : UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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